

# 2SC1226, 2SC1226A

Silicon NPN Epitaxial Planar Type

Medium Power Amplifier

Complementary Pair with 2SA699, 2SA699A

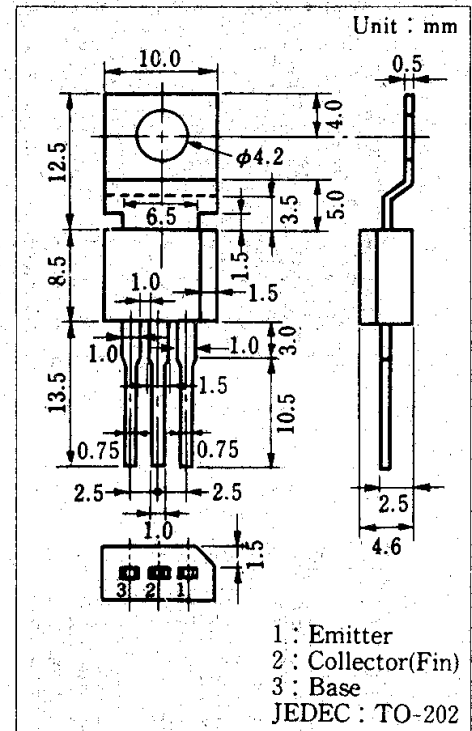
### Feature

- 5W output in complementary pair with 2SA699, 2SA699A

### Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Value	Unit
Collector-base voltage	2SC1226	40	V
	2SC1226A	50	
Collector-emitter voltage	2SC1226	32	V
	2SC1226A	40	
Emitter-base voltage	$V_{EBO}$	5	V
Peak collector current	$I_{CP}$	3	A
Base current	$I_B$	0.6	A
Collector power dissipation (Tc=25°C)	$P_C$	10	W
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 ~ +150	°C

### Package Dimensions



### Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB}=20\text{ V}, I_E=0$			1	$\mu\text{A}$
	$I_{CEO}$	$V_{CE}=12\text{ V}, I_B=0$			100	
Emitter cutoff current	$I_{EBO}$	$V_{EB}=5\text{ V}, I_C=0$			100	$\mu\text{A}$
Collector-base voltage	$V_{CBO}$	$I_C=1\text{ mA}, I_E=0$	40			V
			50			
Collector-emitter voltage	$V_{CEO}$	$I_C=10\text{ mA}, I_B=0$	32			V
			40			
DC current gain	$h_{FE}^{*1}$	$V_{CE}=5\text{ V}, I_C=1\text{ A}^{*2}$	50	120	220	
Transition frequency	$f_T$	$V_{CE}=5\text{ V}, I_C=0.5\text{ A}^{*2}$		150		MHz
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=2\text{ A}, I_B=0.2\text{ A}^{*2}$			1.5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{ A}, I_B=0.2\text{ A}^{*2}$		0.4	1	V
Collector output capacitance	$C_{ob}$	$V_{CB}=5\text{ V}, I_E=0, f=1\text{ MHz}$		50		pF

\*2 パルス測定

### Classification

Class	P	Q	R
$h_{FE}$	50~100	80~160	120~220